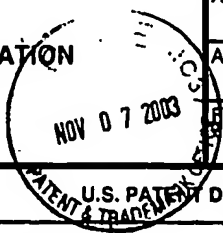


# INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)



ATTY DOCKET NO.  
50033-00006

SERIAL NO.  
10/630,238

APPLICANT(S)  
Van Zeghbroeck, et al

FILING DATE  
July 30, 2003

GROUP  
1765

## U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
LV	a.	H1637	03/04/1997	Offord et al	437	173	
	b.	4,945,394	07/31/1990	Palmour et al	357	34	
	c.	5,266,503	11/30/1993	Wang et al	437	24	
	d.	6,180,958	01/30/2001	Cooper, Jr.	257	77	
	e.	6,181,200	01/30/2001	Titizian et al	330	66	
	f.	6,303,475	10/16/2001	Suvorov et al	438	519	
	g.	6,313,482	11/06/2001	Baliga	257	77	
	h.	6,323,506	11/27/2001	Alok	257	77	
	i.	6,329,675	12/11/2001	Singh et al	257	77	
	j.	6,331,931	12/18/2001	Titizian et al	361	306.3	
LV	k.	6,218,254	04/17/2001	Singh et al	438	364	

## FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

LV		l.	Article entitled "Silicon Carbide Bipolar Transistor" by W. V. Munch and P. Hoeck published in <i>Solid State Electronics</i> , 1978, Vol. 21, pp. 479-480, Pergamon Press, Great Britain
LV		m.	Excerpt from textbook <i>Volume V Introduction to Microelectronic Fabrication</i> , pp. 71-73, author Richard C. Jaeger, Auburn University, published by Addison-Wesley Publishing Company, reprinted with corrections May, 1993.

EXAMINER

LAN VINH

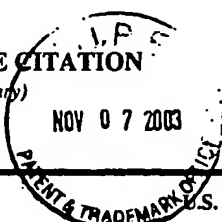
DATE CONSIDERED

7/26/03

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

# INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)



Docket Number (Optional)

50033-00006

Application Number

10/630,238

Applicant(s)

VAN ZEGHBROECK et al

Filing Date

July 30, 2003

Group Art Unit

1765

## U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
LV	n.	5,914,611	06/22/1999	Cheng	324	719	
LV	o.	6,228,665	05/08/2001	Griffith et al	438	14	

## FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

LV	p.	U. S. Patent Application Serial No. 10/360,662, filed on February 7, 2003, entitled "Method of Fabricating Self-Aligned Silicon Carbide Semiconductor Devices", and further identified as Attorney Docket No. 50033-00005
LV	q.	U. S. Patent Application Serial No. 10/339,040, filed on January 9, 2003, entitled "Silicon Carbide Semiconductor Devices with a Regrown Contact Layer", and further identified as Attorney Docket No. 50033-00004.

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